

## N-channel 600 V, 1.5 $\Omega$ , 2.2 A MDmesh™ II Power MOSFET in a PowerFLAT™ 3.3 x 3.3 HV package

Datasheet - production data

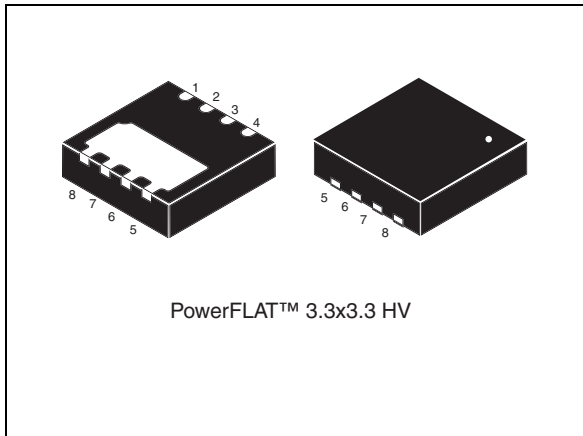
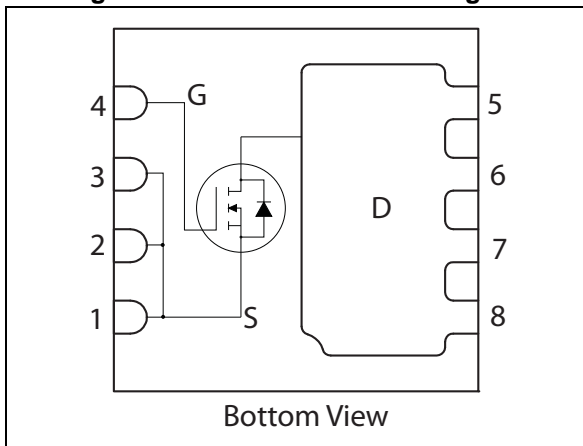


Figure 1. Internal schematic diagram



### Features

Order code	$R_{DS(on)}$ max.	$I_D$
STL3NM60N	1.8 $\Omega$	2.2 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

### Application

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL3NM60N	3NM60N	PowerFLAT™ 3.3 x 3.3 HV	Tape and reel

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	600	V
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	2.2	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100\text{ }^\circ\text{C}$	1.7	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb} = 25\text{ }^\circ\text{C}$	0.65	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb}=100\text{ }^\circ\text{C}$	0.5	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	2.6	A
$P_{TOT}^{(2)}$	Total dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	2	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	22	W
$I_{AS}$	Avalanche current, repetitive or not-repetitive <sup>(3)</sup>	1	A
$E_{AS}$	Single pulse avalanche energy <sup>(4)</sup>	119	mJ
	Derating factor <sup>(2)</sup>	0.016	W/°C
$dv/dt^{(5)}$	Peak diode recovery voltage slope	15	V/ns
$T_J$ $T_{stg}$	Operating junction temperature storage temperature	-55 to 150	°C

1. The value is rated according  $R_{thj-case}$ .
2. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10$  sec
3. Pulse width limited by  $T_{jmax}$
4. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AS}$ ,  $V_{DD} = 50\text{V}$
5.  $I_{SD} \leq 2.2\text{ A}$ ,  $dv/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS\ peak} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	5.6	°C/W
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max.	62.5	°C/W

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10$  sec.

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS}=0$ )	$I_D = 1 \text{ mA}$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS}=0$ )	$V_{DS} = 600 \text{ V}$ ,			1	$\mu\text{A}$
		$V_{DS} = 600 \text{ V}$ , $T_C = 125^{\circ}C$			100	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS}=0$ )	$V_{GS} = \pm 25 \text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}$ , $I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS}=10 \text{ V}$ , $I_D=1 \text{ A}$		1.5	1.8	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{V}$ , $f=1 \text{ MHz}$ , $V_{GS}=0$	-	188	-	pF
$C_{oss}$	Output capacitance		-	13	-	pF
$C_{rss}$	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss \text{ eq.}}^{(1)}$	Output equivalent capacitance	$V_{GS}=0$ , $V_{DS}=0$ to $480 \text{ V}$	-	100	-	pF
$R_g$	Gate input resistance	$f = 1 \text{ MHz}$ gate DC bias=0 test signal level = $20 \text{ mV}$ open drain	-	6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD}=480 \text{ V}$ , $I_D = 2.2 \text{ A}$	-	9.5	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS}=10 \text{ V}$	-	1.6	-	nC
$Q_{gd}$	Gate-drain charge	(see <a href="#">Figure 15</a> )	-	5.3	-	nC

1.  $C_{oss \text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 1.1\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14</a> )	-	8.6	-	ns
$t_r$	Rise time		-	6.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	20.8	-	ns
$t_f$	Fall time		-	20	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		2.2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		8.8	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.2\text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 2.2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 16</a> )	-	168		ns
$Q_{rr}$	Reverse recovery charge		-	672		nC
$I_{RRM}$	Reverse recovery current		-	8		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 2.2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 16</a> )	-	2.3		ns
$Q_{rr}$	Reverse recovery charge		-	913		nC
$I_{RRM}$	Reverse recovery current		-	9		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

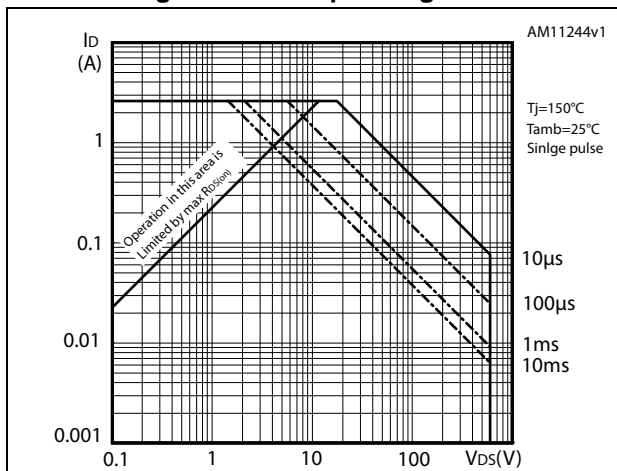


Figure 3. Thermal impedance

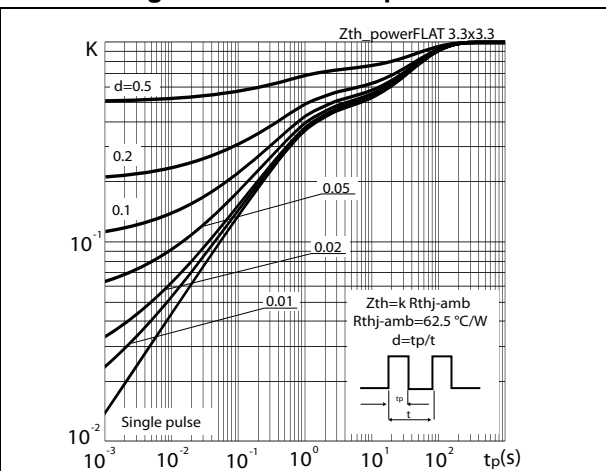


Figure 4. Output characteristics

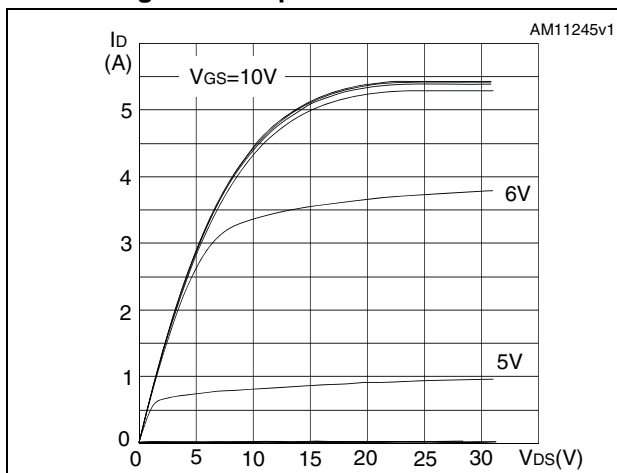


Figure 5. Transfer characteristics

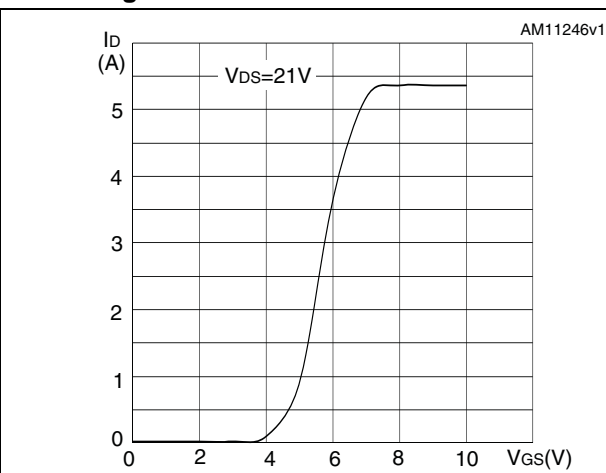


Figure 6. Gate charge vs gate-source voltage

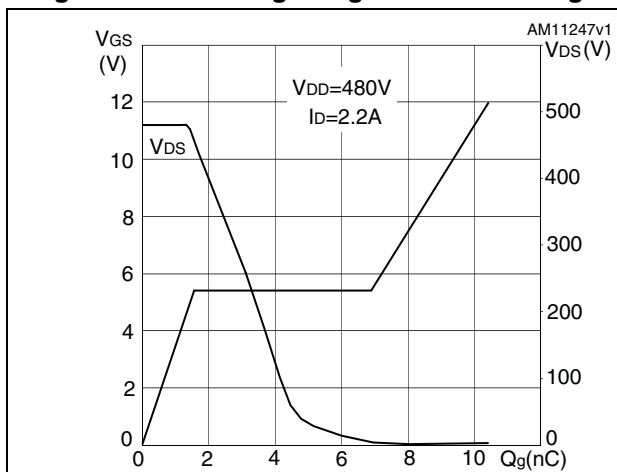


Figure 7. Static drain-source on resistance

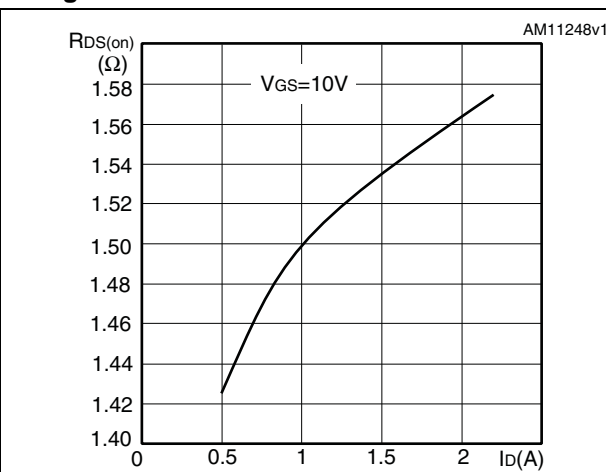


Figure 8. Capacitance variations

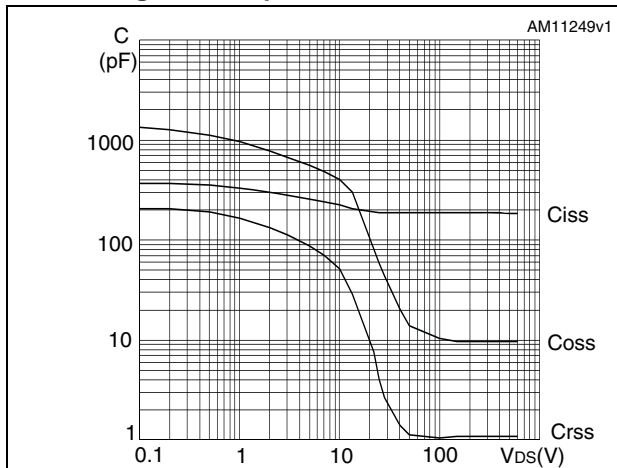


Figure 9. Output capacitance stored energy

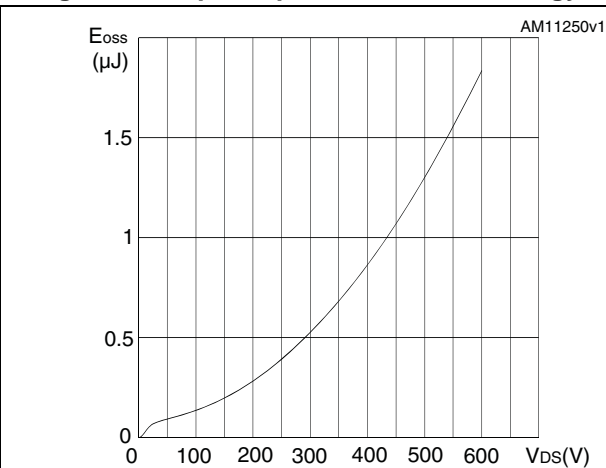


Figure 10. Normalized gate threshold voltage vs temperature

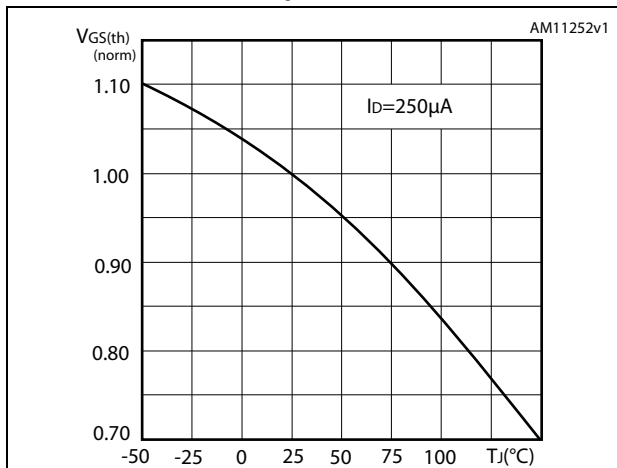


Figure 11. Normalized on resistance vs temperature

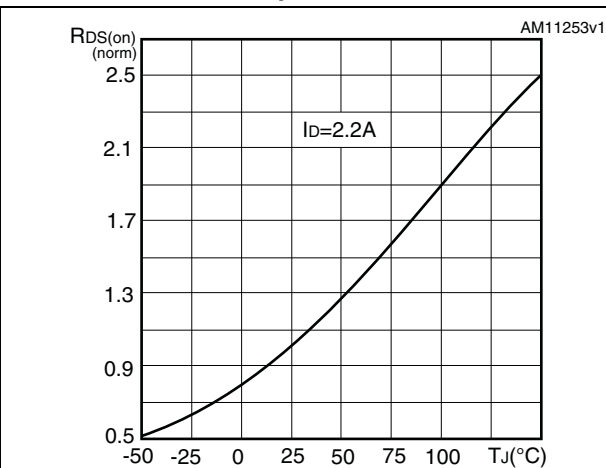


Figure 12. Normalized V(BR)DSS vs temperature

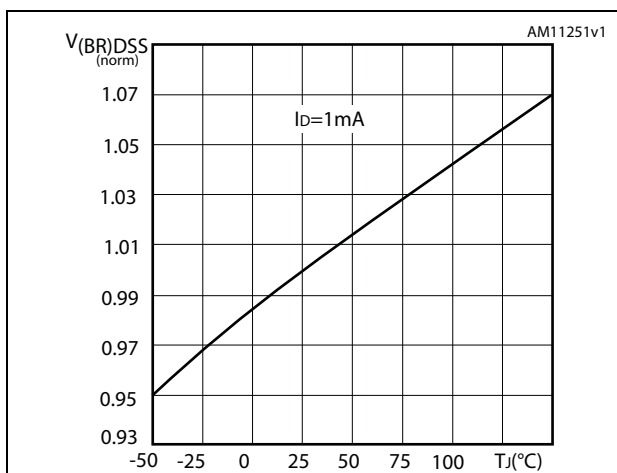
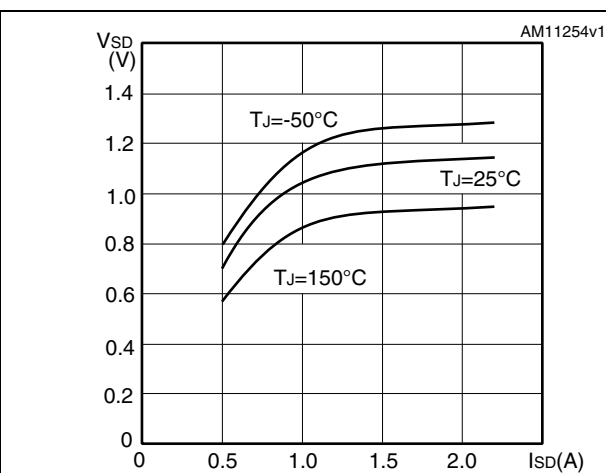


Figure 13. Source-drain diode forward characteristics



### 3 Test circuits

Figure 14. Switching times test circuit for resistive load



Figure 15. Gate charge test circuit



Figure 16. Test circuit for inductive load switching and diode recovery times



Figure 17. Unclamped inductive load test circuit



Figure 18. Unclamped inductive waveform

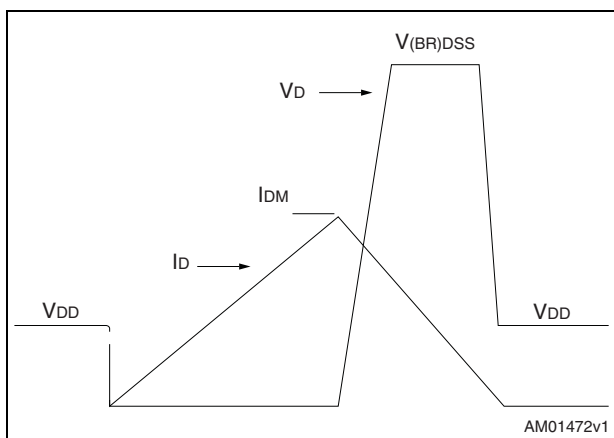
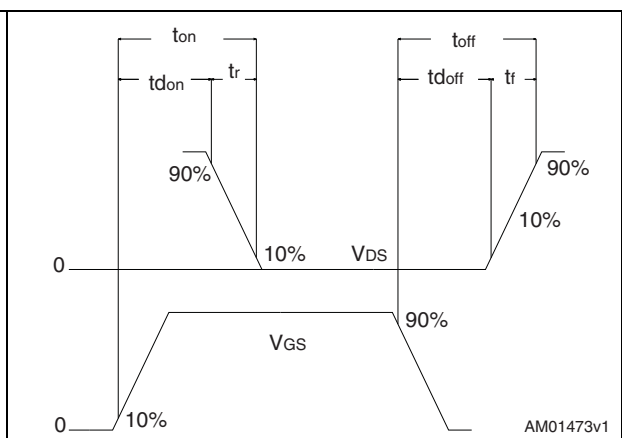


Figure 19. Switching time waveform





## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 20. PowerFLAT™ 3.3 x 3.3 HV drawing

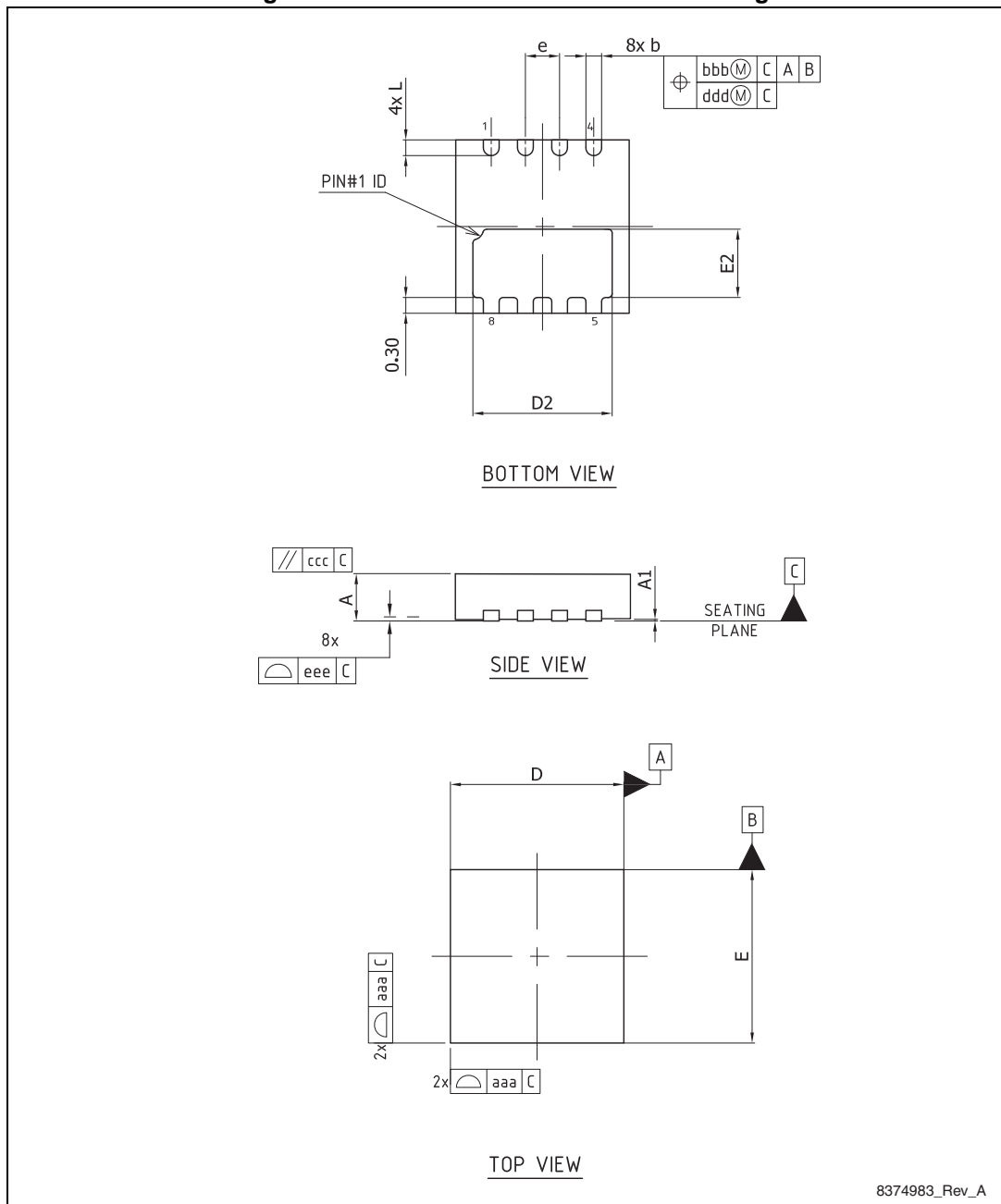
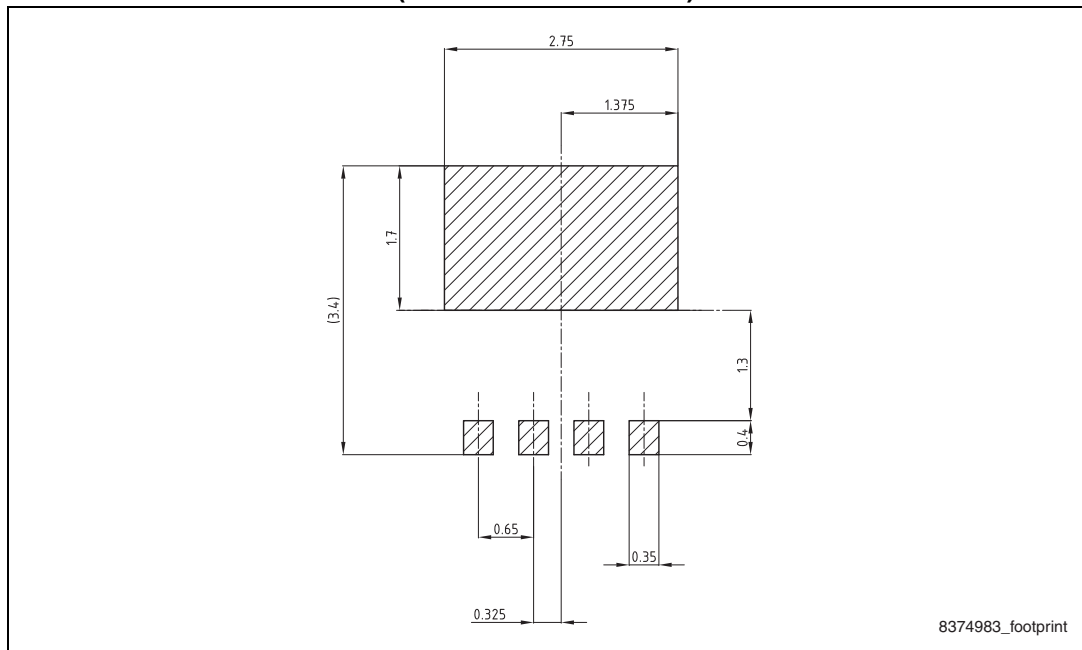


Table 8. PowerFLAT™ 3.3 x 3.3 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0	0.02	0.05
b	0.25	0.30	0.40
D		3.30	
D2	2.50	2.65	2.75
E		3.30	
E2	1.15	1.30	1.40
e		0.65	
L	0.20	0.30	0.40
aaa		0.10	
bbb		0.10	
ccc		0.10	
ddd		0.05	
eee		0.08	

Figure 21. PowerFLAT™ 3.3 x 3.3 HV recommended footprint (dimensions are in mm)



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
12-Mar-2012	1	First release.
19-Nov-2014	2	Document status changed from preliminary to production data. Updated <i>Figure 1.: Internal schematic diagram</i> , <i>Figure 2.: Safe operating area</i> , <i>Figure 3.: Thermal impedance</i> and <i>Figure 12.: Normalized <math>V_{(BR)DSS}</math> vs temperature</i> . Updated <i>Table 5.: Dynamic</i> and <i>Table 7.: Source drain diode</i> . Minor text changes.

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